2SJ633



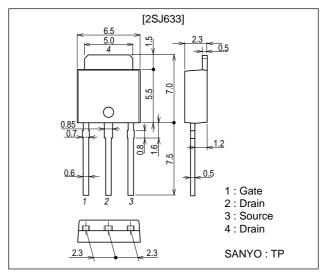
# **DC / DC Converter Applications**

#### **Features**

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- · 4V drive.

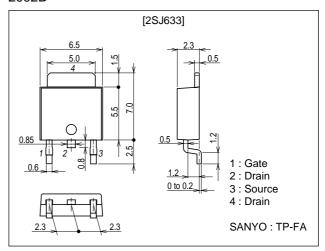
### **Package Dimensions**

unit : mm 2083B



### **Package Dimensions**

unit : mm 2092B



- Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.
- SANYO assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO products described or contained herein.

## **Specifications**

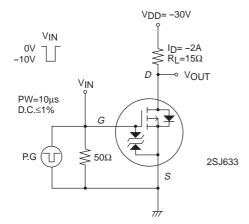
### **Absolute Maximum Ratings** at Ta=25°C

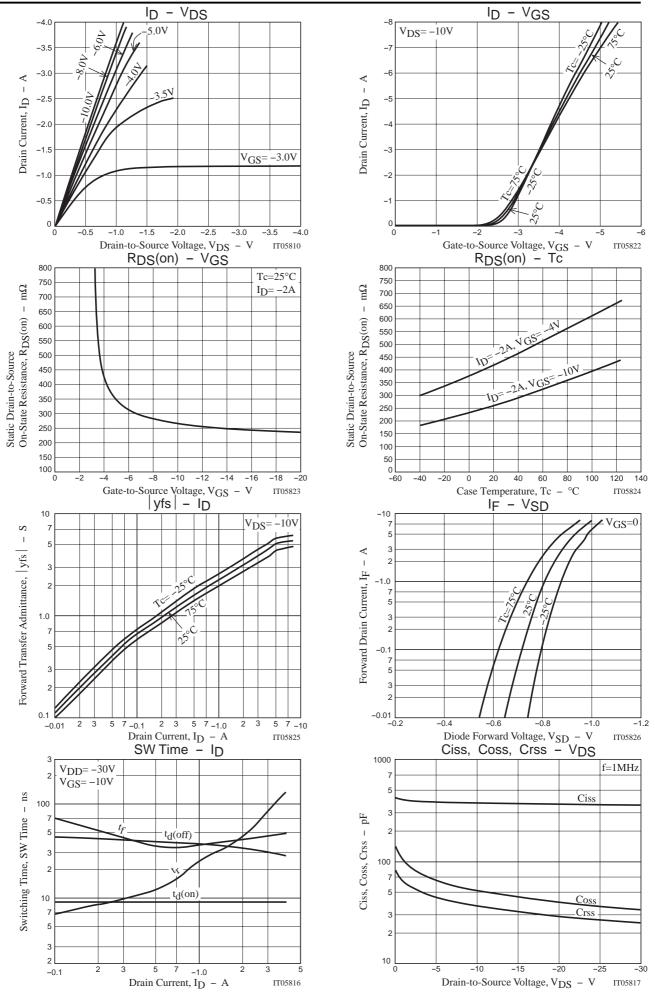
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-60	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-4	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-16	Α
Allowable Power Dissipation	PD		1	W
		Tc=25°C	15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

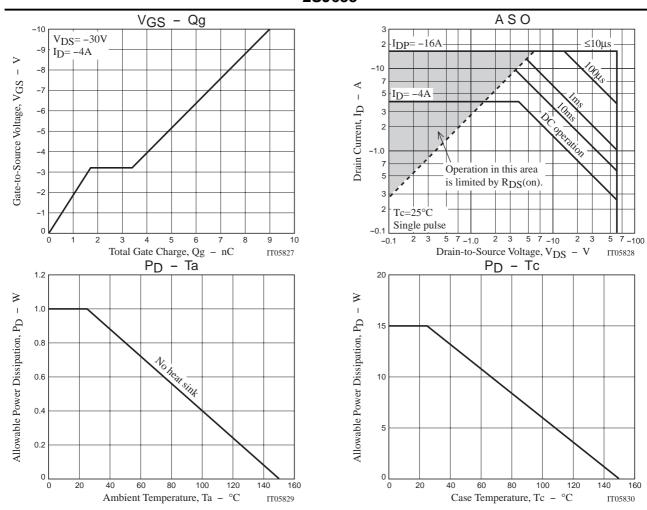
#### **Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>G</sub> S=0	-60			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A	1.5	3		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =-2A, V <sub>G</sub> S=-10V		280	365	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =-2A, V <sub>G</sub> S=-4V		405	565	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =-20V, f=1MHz		365		pF
Output Capacitance	Coss	V <sub>DS</sub> =-20V, f=1MHz		39		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =-20V, f=1MHz		30		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		9		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		45		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		33		ns
Fall Time	tf	See specified Test Circuit.		41		ns
Total Gate Charge	Qg	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A		9		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A		1.7		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A		1.7		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-4A, V <sub>G</sub> S=0		-0.9	-1.2	V

### **Switching Time Test Circuit**







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